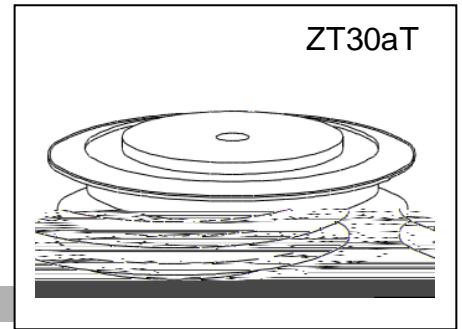




FAST RECOVERY RECTIFIER DIODE

Features:

- . All diffused structure
- . High surge rating
- . Blocking capability up to 3000 volts
- . Soft recovery
- . Ceramic housing hermetic package
- . Pressure assembled device



ELECTRICAL CHARACTERISTICS AND RATINGS

Reverse Blocking

Device Type	V _{RRM} (1)	V _{RSM} (1)
ZK300-20	2000	2200
ZK300-22	2200	2400
ZK300-24	2400	2600
ZK300-26	2600	2800
ZK300-28	2800	3000
ZK300-30	3000	3200

V_{RRM} = Repetitive peak reverse voltage

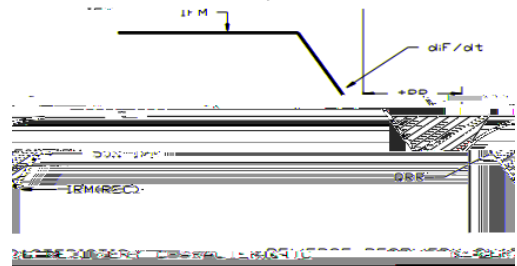
V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse current	I _{RRM}	10 mA 15 mA (3)
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Notes:

All ratings are specified for T_j=25 °C, unless otherwise stated

- (1) All voltage ratings are specified for an applied 50Hz/60Hz sinusoidal waveform over the temperature range -40 to +125°C.
- (2) 10 msec. max. pulse width
- (3) Maximum value for T_j = 125°C.
- (4) See parameter definition below :



Conducting - on state

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Average forward current	I _{F(AV)}		300		A	Sinewave 180°, T _c = 70
RMS forward current	I _{FRMS}		471		A	
Peak one cycle surge (non repetitive) current	I _{FSM}		4800		A	10 msec (50Hz), sinusoidal wave-shape, 180° conduction, T _j = 125
I square t	I ² t		115200		A ² s	8.3 msec and 10.0 msec
Peak forward voltage	V _{FM}		2.40		V	I _{FM} = 1200A; Duty cycle 0.01%
Reverse Recovery Current (4)	I _{RM(REC)}		*		A	I _{FM} = 1000 A; dI _F /dt = 10 A/ s; T _j max
Reverse Recovery Charge (4)	Q _{rr}		*		μC	I _{FM} = 1000 A; dI _F /dt = 10 A/ s; T _j max
Reverse Recovery Time (4)	t _{rr}		6		μs	I _{FM} = 1000 A; dI _F /dt = 10 A/ s; T _j max

* For guaranteed maximum values, contact factory

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